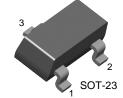


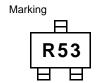
KSR2103

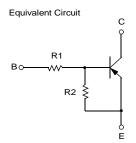
Switching Application (Bias Resistor Built In)

- Switching circuit, Inverter, Interface circuit, Driver Circuit
- Built in bias Resistor ($R_1=22K\Omega$, $R_2=22K\Omega$)
- Complement to KSR1103



1. Base 2. Emitter 3. Collector





PNP Epitaxial Silicon Transistor

Absolute Maximum Ratings Ta=25°C unless otherwise noted

Symbol	Parameter	Value	Units
V_{CBO}	Collector-Base Voltage	-50	V
V_{CEO}	Collector-Emitter Voltage	-50	V
V _{EBO}	Emitter-Base Voltage	-10	V
I _C	Collector Current	-100	mA
P _C	Collector Power Dissipation	200	mW
T _J	Junction Temperature	150	°C
T _{STG}	Storage Temperature	-55 ~ 150	°C

Electrical Characteristics T_a =25°C unless otherwise noted

Symbol	Parameter	Test Condition	Min.	Тур.	Max.	Units
BV _{CBO}	Collector-Base Breakdown Voltage	I_{C} = -10 μ A, I_{E} =0	-50			V
BV _{CEO}	Collector-Emitter Breakdown Voltage	I _C = -100μA, I _B =0	-50			V
I _{CBO}	Collector Cutoff Current	V _{CB} = -40V, I _E =0			-0.1	μΑ
h _{FE}	DC Current Gain	V_{CE} = -5V, I_{C} = -5mA	56			
V _{CE} (sat)	Collector-Emitter Saturation Voltage	I _C = -10mA, I _B = -0.5mA			-0.3	V
f _T	Current Gain Bandwidth Product	V _{CE} = -10V, I _C = -5mA		200		MHz
C _{ob}	Output Capacitance	V _{CB} = -10V, I _E =0 f=1.0MHz		5.5		pF
V _I (off)	Input Off Voltage	V_{CE} = -5V, I_{C} = -100 μ A	-0.5			V
V _I (on)	Input On Voltage	$V_{CE} = -0.3V, I_{C} = -5mA$			-3.0	V
R ₁	Input Resistor		15	22	29	ΚΩ
R ₁ /R ₂	Resistor Ratio		0.9	1	1.1	

Typical Characteristics

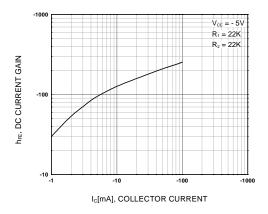


Figure 1. DC current Gain

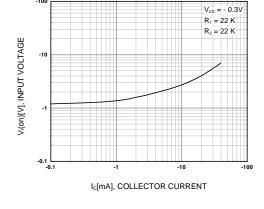


Figure 2. Input On Voltage

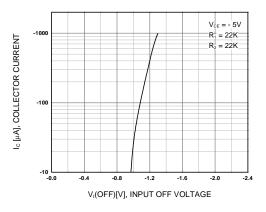


Figure 3. Input Off Voltage

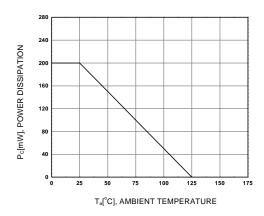
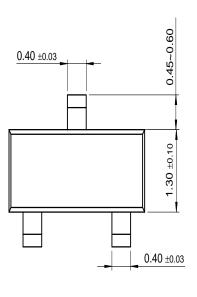
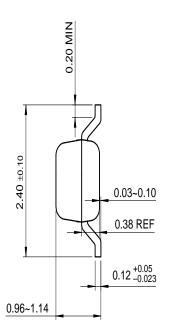


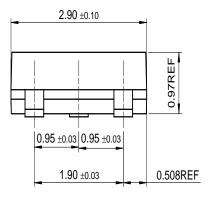
Figure 4. Power Derating

Package Dimensions

SOT-23







Dimensions in Millimeters

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EcoSPARK™	GTO™	MSX™	QT Optoelectronics™	TinyLogic™
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EnSigna™	I^2C^{TM}	OCX^{TM}	RapidConfigure™	UHC™
Across the board.	Around the world.™	OCXPro™	RapidConnect™	UltraFET [®]
The Power Franci	hise™	OPTOLOGIC [®]	SILENT SWITCHER®	VCX TM
Programmable Ad	ctive Droop™	OPTOPLANAR™	SMART START™	

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KSR2103

PNP Epitaxial Silicon Transistor

Contents

- Features
- Product status/pricing/packaging
- Order Samples
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Features

Switching Application (Bias Resister Built In)

- Switchng circuit, Inverter, Interface circuit, Driver Circuit
- Built in bias Resistor (R₁=22KΩ, R₂=22KΩ)
- Complement to KSR1103

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Product status/pricing/packaging

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KSR2103MTF_NL	Lifetime Buy	Ø	<u>SOT-23</u>	3	TAPE REEL	

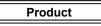


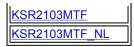
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Qualification Support

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